

SCHOTTKY BARRIER DIODE

Features

- (1) Small surface mounting type SC-76/SOD-323
- (2) Low reverse current and low forward voltage.
- (3) High reliability
- (4) Pb-Free package is available.

Construction

silicon epitaxial planar

LRB751V- 40T1



SC-76/SOD-323

ORDERING INFORMATION

Device	Package	Shipping
LRB751V-40T1	SOD-323/SC-76	3000/Tape&Reel
LRB751V-40T1G (Pb-Free)	SOD-323/SC-76	3000/Tape&Reel



MAXIMUM RATINGS (T_A = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	V _R	30	V
Mean rectifying current	I _O	30	mA
Peak forward surge current*	I _{FSM}	200	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40~+125	°C

*60Hz for 1

DEVICE MARKING

LRB751V-40T1= 5E

ELECTRICAL CHARACTERISTICS(T_A = 25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Forward voltage	V _F	—	—	0.37	V	I _F =1mA
Reverse current	I _R	—	—	0.5	μA	V _R =30V
Capacitance between terminals	C _T	—	2.0	—	pF	V _R =1V, f=1MHz

LRB751V-40T1

Electrical characteristic curves($T_A = 25^\circ\text{C}$)

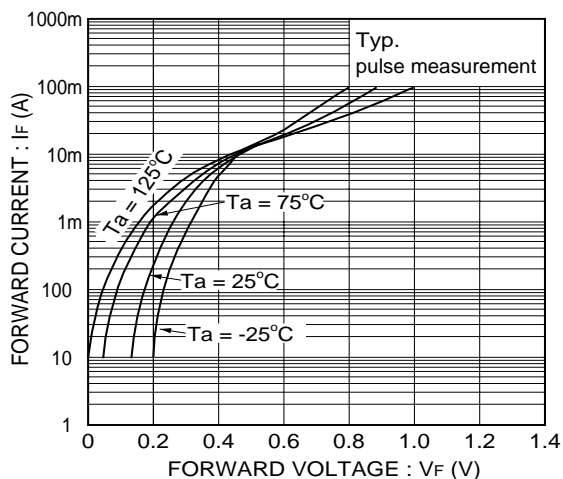


Fig. 1 Forward characteristics

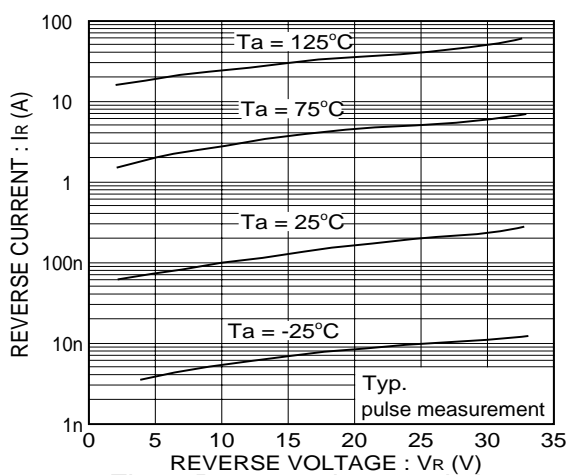


Fig. 2 Reverse characteristics

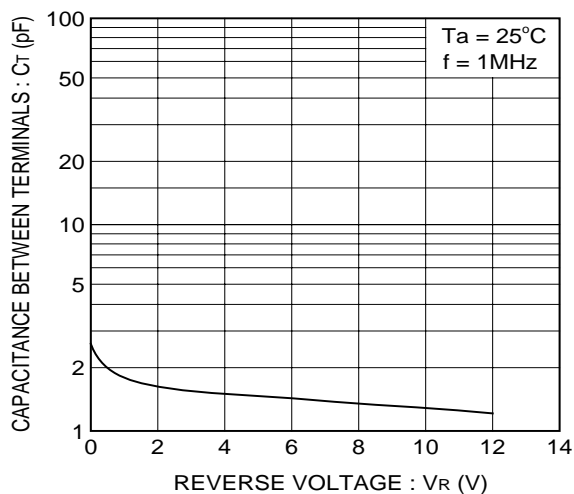
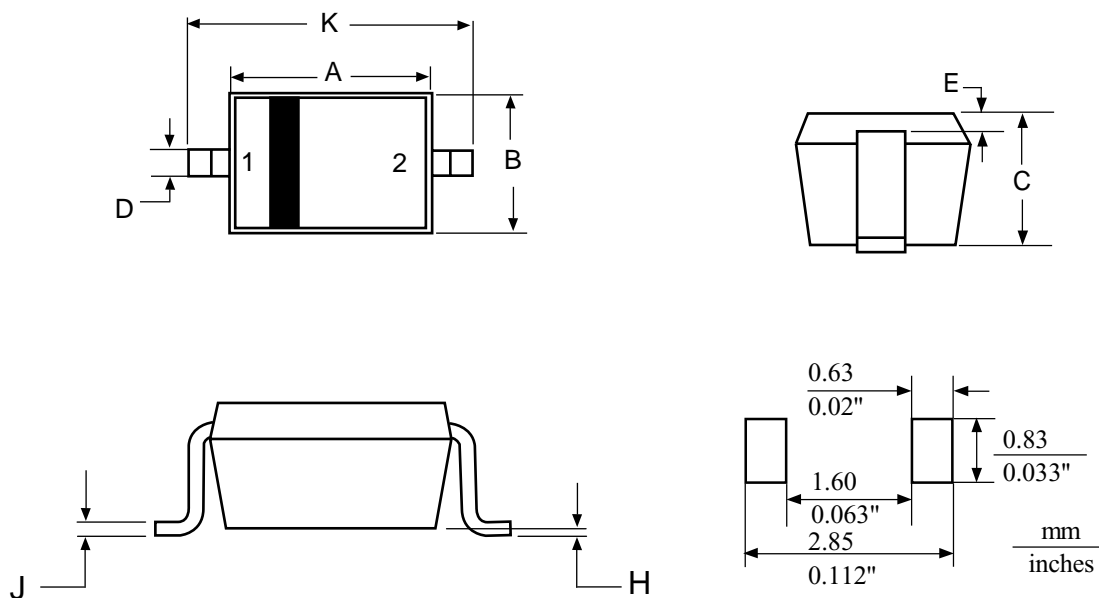


Fig. 3 Capacitance between terminals characteristics

LRB751V- 40T1
SOD-323

NOTES:

1. DIMENSIONING AND TOLERANCING
PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.60	1.80	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.80	1.00	0.031	0.039
D	0.25	0.40	0.010	0.016
E	0.15 REF		0.006 REF	
H	0.00	0.10	0.000	0.004
J	0.089	0.177	0.0035	0.0070
K	2.30	2.70	0.091	0.106

PIN:1:CATHODE
2:ANODE